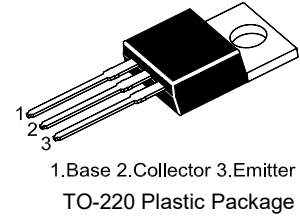


2SD1163A

NPN Silicon Epitaxial Planar Transistor

for TV horizontal deflection output applications

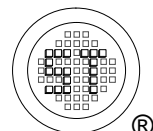


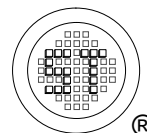
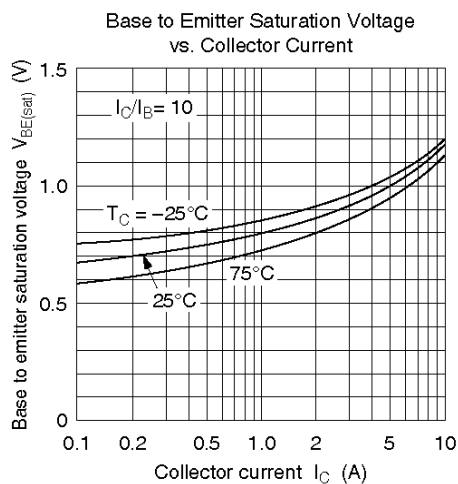
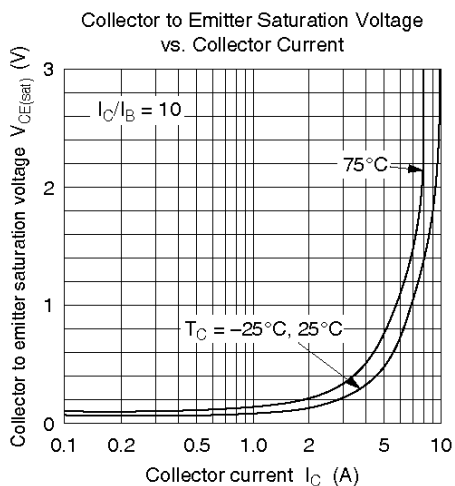
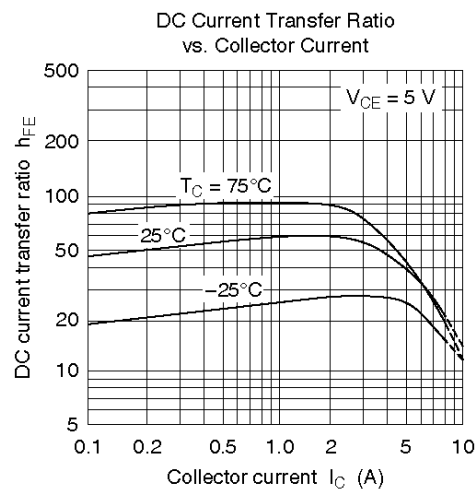
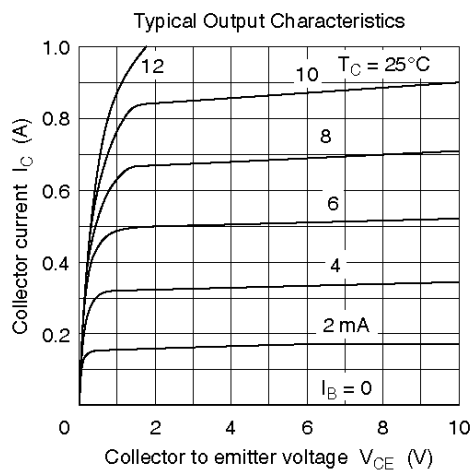
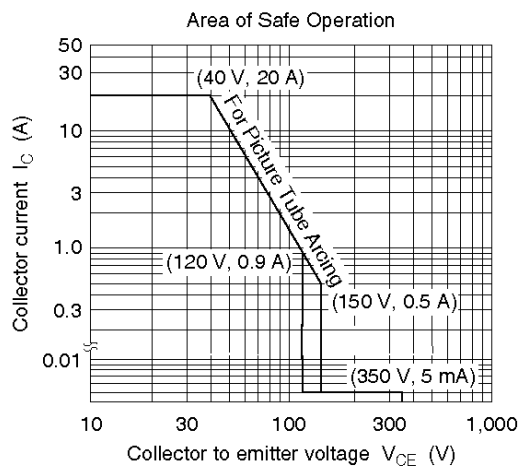
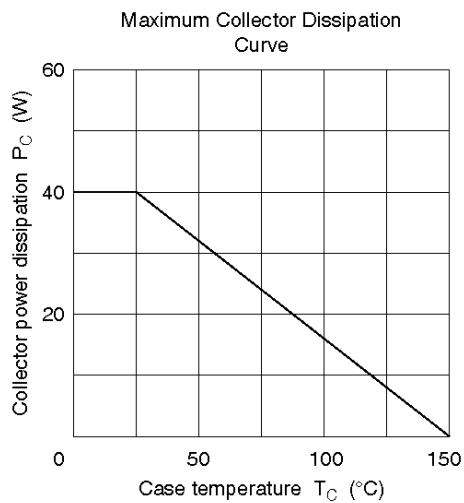
Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	350	V
Collector Emitter Voltage	V_{CEO}	150	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	7	A
Collector Peak Current	I_{CP}	10	A
Collector Surge Current	$I_{C(surge)}$	20	A
Power Dissipation ($T_c = 25\text{ }^{\circ}\text{C}$)	P_{tot}	40	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

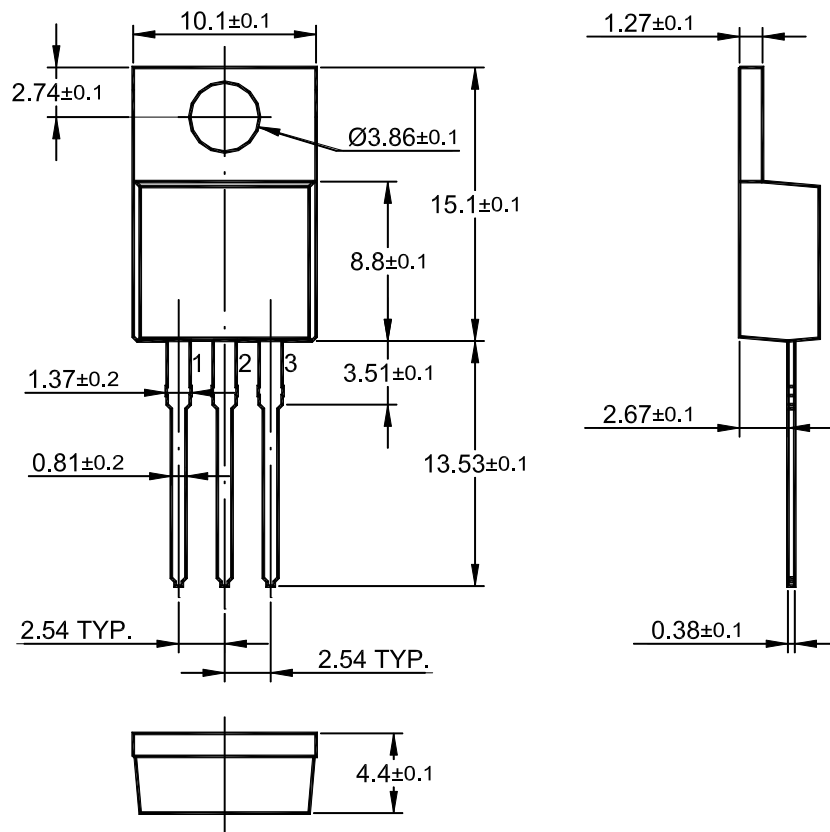
Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 5\text{ A}$	h_{FE}	25	-	-
Collector Base Cutoff Current at $V_{CB} = 350\text{ V}$	I_{CBO}	-	5	mA
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	150	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ mA}$	$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $I_C = 5\text{ A}$, $I_B = 0.5\text{ A}$	$V_{CE(sat)}$	-	1	V
Base Emitter Saturation Voltage at $I_C = 5\text{ A}$, $I_B = 0.5\text{ A}$	$V_{BE(sat)}$	-	1.2	V
Fall Time at $I_{CP} = 3.5\text{ A}$, $I_{B1} = 0.45\text{ A}$	t_f	-	0.5	μs





2SD1163A

TO-220 PACKAGE OUTLINE



Dimensions in mm

